

DFD05T

Diffused Junction Type Silicon Diode

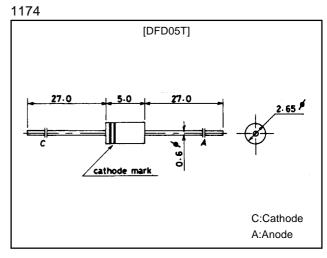
0.5A Power Rectifier

Features

- · High-speed switching use.
- · Plastic molded structure.
- Reverse recovery time trr=0.15µs max (B, C, E, G). trr=0.3µs max (J, L, N, R, T).
- Peak reverse voltage: V_{RM} =100 to 1700V
- · Average rectified current $I_0=0.5A$

Package Dimensions

unit:mm



Specifications

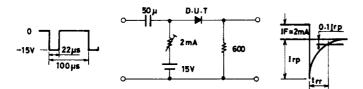
Absolute Maximum Ratings at Ta = 25 C

Parameter	Symbol	Conditions		DF	DFD05TB		D05TC	DFD05TE	DFD05TG	Unit
Peak Reverse Voltage	V _{RM}				100		200	400	600	V
Average Recitified Current	IO	Ta=50°C			\rightarrow		\rightarrow	\rightarrow	0.5	А
Surge Forward Current	IFSM	50Hz sine wave, 1cycle			\rightarrow		\rightarrow	\rightarrow	30	А
Junction Temperature	Tj				\rightarrow		\rightarrow	\rightarrow	150	°C
Storage Temperature	Tstg				\rightarrow		\rightarrow	\rightarrow	-40 to +150	°C
Parameter	Symbol	Conditions	DFD0	5TJ	DFD05T	rl C	OFD05TN	DFD05TR	DFD05TT	Unit
Peak Reverse Voltage	V _{RM}			800	10	00	1200	1500	1700	V
Average Recitified Current	IO	Ta=50°C		\rightarrow		\rightarrow	\rightarrow	\rightarrow	0.5	А
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	\rightarrow			\rightarrow	\rightarrow	\rightarrow	20	A
Junction Temperature	Tj			\rightarrow		\rightarrow	\rightarrow	\rightarrow	125	°C
Storage Temperature	Tstg			\rightarrow		\rightarrow	\rightarrow	\rightarrow	-40 to +150	°C

Electrical Characteristics at Ta = 25 C

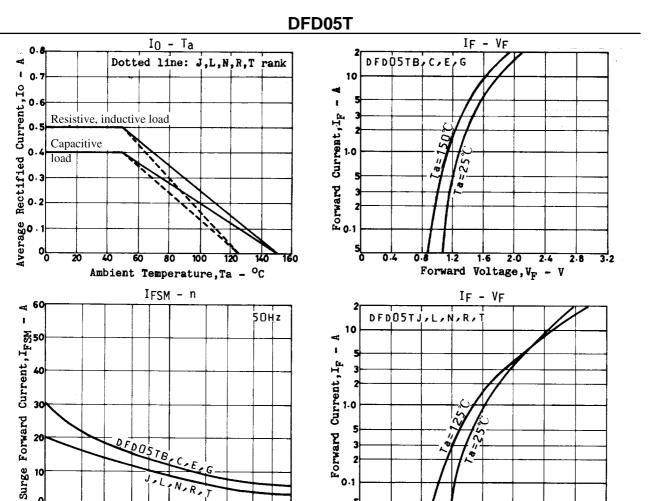
Parameter	Symbol	Conditions		Ratings			
Farameter	Symbol	Conditions	min	typ	max	Unit	
Forward Voltage	V _F	I _F =0.5A (B, C, E, G)			1.2	V	
		I _F =0.5A (J, L, N, R, T)			1.5	V	
Reverse Current	I _R	V _R :At each V _{RM}			10	μΑ	
Reverse Recovery Time	trr	I _F =2mA, V _R =15V (B,C, E, G)			0.15	μs	
		I _F =2mA, VR=15V (J, L, N, R, T)			0.3	μs	

Reverse Recovery Time Test Circuit



Unit (resistance:Ω, capacitance:F)

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100

0.4

0.6

1.2

1.6

Forward Voltage, VF - V

2.0

2.4

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Anyone purchasing any products described or contained herein for an above-mentioned use shall:

R

10

Number of Cycles at 50Hz,n

0 1.0

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